

Silicon – Diode Array

FSA2563P

8 Diode Array

60V/350mA

DATASHEET

OEM – Fairchild

Source: Fairchild Databook 1978

**FSA2563M • FSA2563P • FSA2564M • FSA2564P
FSA2565M • FSA2565P • FSA2566M • FSA2566P**
PLANAR AIR-ISOLATED MONOLITHIC DIODE ARRAYS

- C... 3.0 pf (max)
- V_F ... 15 mV (max) @ 10 mA

ABSOLUTE MAXIMUM RATINGS (Note 1)**Temperatures**

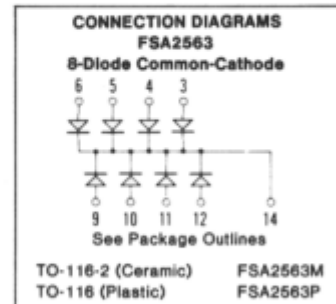
Storage Temperature Range (M Suffix)	-55°C to +200°C
(P Suffix)	-55°C to +150°C
Maximum Junction Operating Temperature	+150°C
Lead Temperature	+260°C

Power Dissipation (Note 2)

Maximum Dissipation per Junction at 25°C Ambient	400 mW
Maximum Dissipation per Package at 25°C Ambient	650 mW
Linear Derating Factor (from 25°C) Junction	3.2 mW/°C
Package	5.2 mW/°C

Maximum Voltage and Currents

WIV	Working Inverse Voltage	40 V
I_F	Continuous Forward Current	350 mA
I_F (surge)	Peak Forward Surge Current	
	Pulse Width = 1.0 s	1.0 A
	Pulse Width = 1.0 μ s	2.0 A

**ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)**

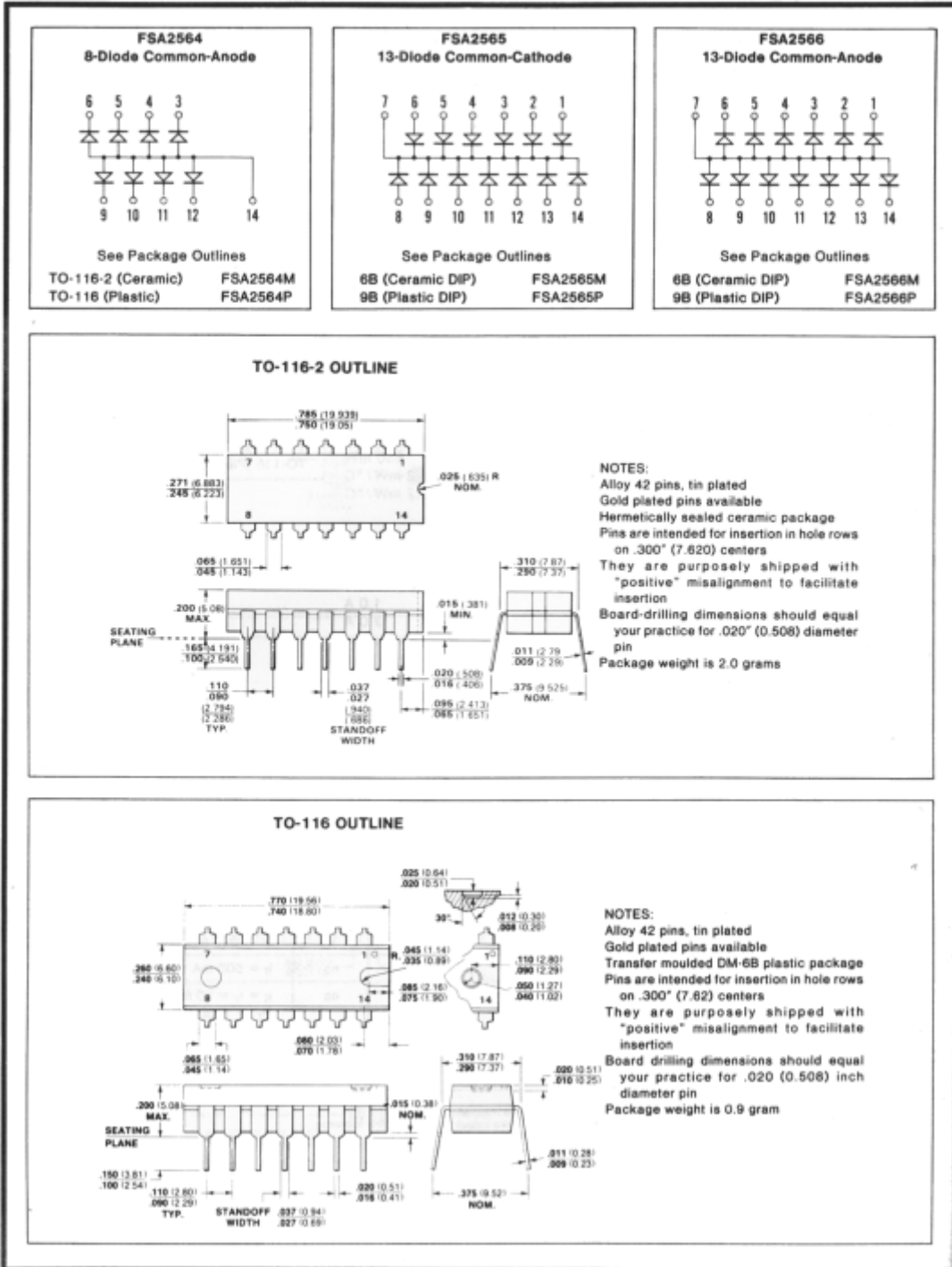
SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
BV	Breakdown Voltage	60		V	$I_R = 10 \mu A$
V_F	Forward Voltage (Note 3)		1.0 1.1 1.3	V V V	$I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$ $I_F = 500 \text{ mA}$
I_R	Reverse Current (Note 4)		100 100	nA μA	$V_R = 40 \text{ V}$ $V_R = 40 \text{ V}, T_A = 125^\circ \text{C}$
C	Capacitance (Note 5)		3	pF	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$
V_{FM}	Peak Forward Voltage (Note 6)		4	V	$I_F = 500 \text{ mA}$
t_{fr}	Forward Recovery Time (Note 6)		40	ns	$I_F = 500 \text{ mA}$
t_{rr}	Reverse Recovery Time (Note 6)		10 50	ns ns	$I_F = I_R = 10 \text{ mA to } 200 \text{ mA}$ $R_L = 100\Omega, I_{rr} = 0.1 I_F$ $I_F = 500 \text{ mA}, I_r = 50 \text{ mA}$ $R_L = 100\Omega, I_{rr} = 5 \text{ mA}$
ΔV_F	Forward Voltage Match (Note 6)		15	mV	$I_F = 10 \text{ mA}$

NOTES:

- These ratings are limiting values above which life or satisfactory performance may be impaired.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.
- V_F is measured using an 8 μ s pulse.
- See test circuits (Note 6) for measurement of reverse current of an individual diode.
- The capacitance is measured from pin-to-pin across any one of the diodes. The interaction of other diodes is therefore included in the measured value.
- For product family characteristic curves and test circuits, refer to Chapter 4, D15.

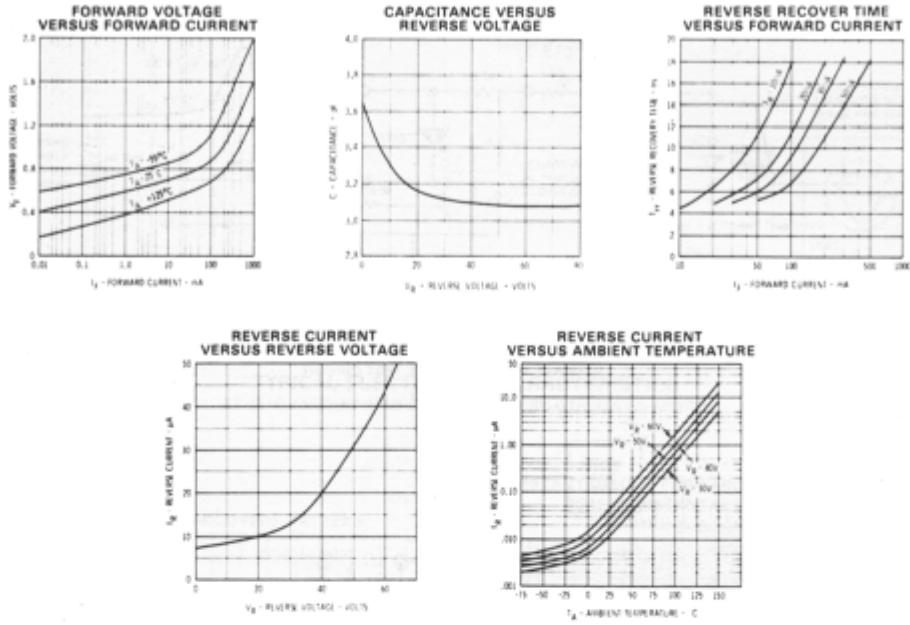
*COMMON ANODE, COMMON CATHODE

FAIRCHILD • DIODE ARRAYS



CURVE SET NUMBER D15
AIR-ISOLATED MONOLITHIC DIODE ARRAY

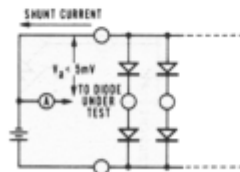
TYPICAL ELECTRICAL CHARACTERISTIC CURVES
 AT 25°C AMBIENT TEMPERATURE UNLESS OTHERWISE NOTED



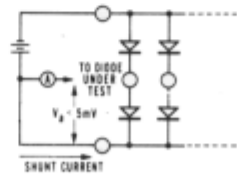
TEST CIRCUITS

To measure reverse current of an individual diode, the following test circuits are used:

COMMON CATHODE DIODES



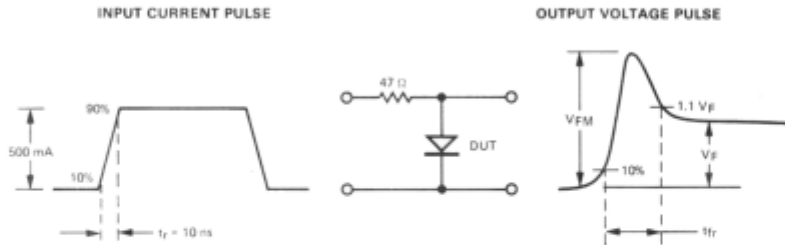
COMMON ANODE DIODES



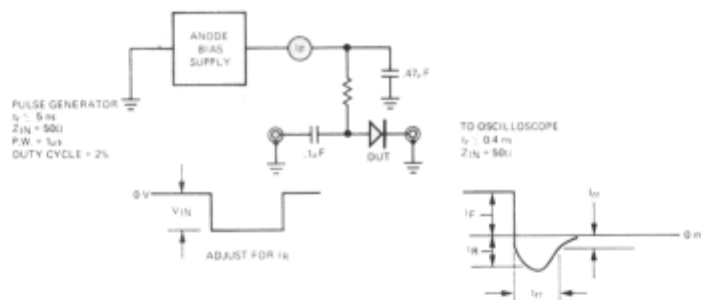
CURVE SET NUMBER D15
AIR-ISOLATED MONOLITHIC DIODE ARRAY

TEST CIRCUITS

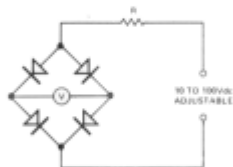
Test requirement for V_{FM} and t_{rr} is as shown below; all leads should be as short as possible.



t_{rr} - REVERSE RECOVERY TIME TEST CIRCUIT
 $I_F = I_R = I_{rr} = 0.1 I_F$

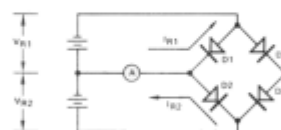


ΔV_F BRIDGE MATCHING CIRCUIT



- NOTES:**
- R Varies depending on the current range. For the most often used current ranges, R is as follows:
- | Current Range (amperes) | R (ohms) |
|-----------------------------|------------|
| 10^{-5} to 10^{-4} | 10^6 |
| 10^{-4} to 10^{-3} | 10^5 |
| 10^{-3} to 10^{-2} | 10^4 |
| or 10^{-n} to 10^{-n+1} | 10^{n+1} |
- V indicates mismatch of assembly.

ΔI_R BRIDGE MATCHING CIRCUIT



- NOTES:**
- $V_{R2} = V_{R1} \pm 1\%$.
 - $I_{R2} - I_{R1} = \Delta I_R$ (difference in I_R between diodes D1 & D2). To measure diodes D3 & D4, reverse cathode-anode terminal connections.
 - A is a center reading pico ammeter. ΔI_R indicated directly on A.